Fernando A. Ponce

List of Publications by Year
in descending order

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354	13,122	28274	29157
papers	citations	55 h-index	104 g-index

357	357	357	7559
all docs	docs citations	times ranked	citing authors

#	Article	IF	Citations
1	Nitride-based semiconductors for blue and green light-emitting devices. Nature, 1997, 386, 351-359.	27.8	1,550
2	High dislocation densities in high efficiency GaNâ€based lightâ€emitting diodes. Applied Physics Letters, 1995, 66, 1249-1251.	3.3	961
3	Defects in single-crystal silicon induced by hydrogenation. Physical Review B, 1987, 35, 4166-4169.	3.2	432
4	Spatial distribution of the luminescence in GaN thin films. Applied Physics Letters, 1996, 68, 57-59.	3.3	361
5	Luminescence from stacking faults in gallium nitride. Applied Physics Letters, 2005, 86, 021908.	3.3	315
6	Selfâ€limiting oxidation for fabricating subâ€5 nm silicon nanowires. Applied Physics Letters, 1994, 64, 1383-1385.	3.3	270
7	Epitaxial MgO on Si(001) for Yâ€Baâ€Cuâ€O thinâ€film growth by pulsed laser deposition. Applied Physics Letters, 1991, 58, 2294-2296.	3.3	237
8	Determination of lattice polarity for growth of GaN bulk single crystals and epitaxial layers. Applied Physics Letters, 1996, 69, 337-339.	3.3	227
9	Edge and screw dislocations as nonradiative centers in InGaN/GaN quantum well luminescence. Applied Physics Letters, 2001, 78, 2691-2693.	3.3	218
10	Microstructure of GaN epitaxy on SiC using AlN buffer layers. Applied Physics Letters, 1995, 67, 410-412.	3.3	200
11	Slip systems and misfit dislocations in InGaN epilayers. Applied Physics Letters, 2003, 83, 5187-5189.	3.3	194
12	Characterization of dislocations in GaN by transmission electron diffraction and microscopy techniques. Applied Physics Letters, 1996, 69, 770-772.	3.3	184
13	Improvement of peak quantum efficiency and efficiency droop in III-nitride visible light-emitting diodes with an InAlN electron-blocking layer. Applied Physics Letters, 2010, 96, .	3.3	183
14	Self-limiting oxidation of Si nanowires. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 1993, 11, 2532.	1.6	149
15	Initial stages of epitaxial growth of GaAs on (100) silicon. Journal of Applied Physics, 1987, 61, 1856-1859.	2.5	148
16	Crystalline structure of AlGaN epitaxy on sapphire using AlN buffer layers. Applied Physics Letters, 1994, 65, 2302-2304.	3.3	140
17	Microstructure and electronic properties of InGaN alloys. Physica Status Solidi (B): Basic Research, 2003, 240, 273-284.	1.5	131
18	MOVPE growth of GaN on Si(111) substrates. Journal of Crystal Growth, 2003, 248, 556-562.	1.5	125

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19	Exciton freeze-out and thermally activated relaxation at local potential fluctuations in thick AlxGa1â”'xN layers. Journal of Applied Physics, 2004, 95, 4670-4674.	2.5	119
20	Metalorganic chemical vapor phase epitaxy of gallium-nitride on silicon. Physica Status Solidi C: Current Topics in Solid State Physics, 2003, 0, 1583-1606.	0.8	116
21	Strained Ga/sub x/In/sub 1-x/P/(AlGa)/sub 0.5/In/sub 0.5/P heterostructures and quantum-well laser diodes. IEEE Journal of Quantum Electronics, 1994, 30, 593-607.	1.9	115
22	Atomic arrangement at the AlN/Si (111) interface. Applied Physics Letters, 2003, 83, 860-862.	3.3	114
23	Dislocation annihilation by silicon delta-doping in GaN epitaxy on Si. Applied Physics Letters, 2002, 81, 4712-4714.	3.3	109
24	Homoepitaxy of GaN on polished bulk single crystals by metalorganic chemical vapor deposition. Applied Physics Letters, 1996, 68, 917-919.	3.3	107
25	Hydrogen in crystalline semiconductors. Physica B: Condensed Matter, 1991, 170, 3-20.	2.7	104
26	Thermodynamic and kinetic considerations on the equilibrium shape for thermally induced microdefects in Czochralski silicon. Journal of Applied Physics, 1986, 59, 3255-3266.	2.5	96
27	Defects and Interfaces in GaN Epitaxy. MRS Bulletin, 1997, 22, 51-57.	3.5	93
28	Oxidation of sub-50 nm Si columns for light emission study. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 1992, 10, 2846.	1.6	92
29	Improvement of quantum efficiency by employing active-layer-friendly lattice-matched InAlN electron blocking layer in green light-emitting diodes. Applied Physics Letters, 2010, 96, .	3.3	89
30	Observation of coreless dislocations in Î±-GaN. Journal of Crystal Growth, 1997, 178, 201-206.	1.5	87
31	Reactions at the interfaces of thin films of Yâ€Baâ€Cuâ€•and Zrâ€oxides with Si substrates. Journal of Applied Physics, 1991, 69, 2176-2182.	2.5	85
32	Ion milled tips for scanning tunneling microscopy. Applied Physics Letters, 1987, 50, 696-698.	3.3	83
33	Efficiency droop due to electron spill-over and limited hole injection in III-nitride visible light-emitting diodes employing lattice-matched InAlN electron blocking layers. Applied Physics Letters, 2012, 101, .	3.3	80
34	Pulsed lateral epitaxial overgrowth of aluminum nitride on sapphire substrates. Applied Physics Letters, 2006, 89, 081905.	3.3	79
35	Low-threshold stimulated emission at 249â€‰nm and 256â€‰nm from AlGaN-based multiple-quantum-well lasers grown on sapphire substrates. Applied Physics Letters, 2014, 105, .	3.3	78
36	Deep-ultraviolet lasing at 243â€‰nm from photo-pumped AlGaN/AlN heterostructure on AlN substrate. Applied Physics Letters, 2013, 102, .	3.3	77

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37	Preparation of oriented Biâ€Caâ€Srâ€Cuâ€O thin films using pulsed laser deposition. Applied Physics Letters, 1988, 53, 337-339.	3.3	76
38	Atomic arrangement at the AlN/SiC interface. Physical Review B, 1996, 53, 7473-7478.	3.2	75
39	Direct imaging of impurityâ€induced Raman scattering in GaN. Applied Physics Letters, 1996, 69, 2650-2652.	3.3	71
40	Light emission and microstructure of Mg-doped AlGaN grown on patterned sapphire. Applied Physics Letters, 2003, 82, 349-351.	3.3	71
41	Prismatic stacking faults in epitaxially laterally overgrown GaN. Applied Physics Letters, 2006, 88, 141912.	3.3	69
42	Synthesis and luminescence properties of ZnO nanostructures produced by the solâ€“gel method. Journal of Crystal Growth, 2008, 310, 599-603.	1.5	64
43	Misfit Strain Relaxation by Stacking Fault Generation in InGaN Quantum Wells Grown onm-Plane GaN. Applied Physics Express, 0, 2, 041002.	2.4	64
44	Structure of thermally induced microdefects in Czochralski silicon after highâ€temperature annealing. Applied Physics Letters, 1983, 43, 1051-1053.	3.3	63
45	Atomic motion on the surface of a cadmium telluride single crystal. Nature, 1981, 290, 386-388.	27.8	62
46	Interface structure in heteroepitaxial CdTe on GaAs(100). Surface Science, 1986, 168, 564-570.	1.9	62
47	Resonant tunneling in GaAs/AlAs heterostructures grown by metalorganic chemical vapor deposition. Applied Physics Letters, 1985, 46, 285-287.	3.3	61
48	Generation of misfit dislocations by basal-plane slip in InGaNâˆ•GaN heterostructures. Applied Physics Letters, 2006, 89, 201911.	3.3	61
49	Structural and optical properties of nonpolar GaN thin films. Applied Physics Letters, 2008, 92, .	3.3	61
50	Control of quantum-confined Stark effect in InGaNâˆ•GaN multiple quantum well active region by p-type layer for III-nitride-based visible light emitting diodes. Applied Physics Letters, 2008, 92, .	3.3	60
51	Engineered Schottky barrier diodes for the modification and control of Schottky barrier heights. Journal of Applied Physics, 1987, 61, 5159-5169.	2.5	59
52	Effect of interface chemistry on the growth of ZnSe on the Si(100) surface. Physical Review B, 1992, 45, 13400-13406.	3.2	58
53	Low Stokes shift in thick and homogeneous InGaN epilayers. Applied Physics Letters, 2002, 80, 550-552.	3.3	58
54	High critical current densities in epitaxial YBa2Cu3O7âˆ’Î´thin films on siliconâ€onâ€sapphire. Applied Physics Letters, 1991, 58, 2432-2434.	3.3	57

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55	Epitaxial BaTiO3/MgO Structure Grown on GaAs(100) by Pulsed Laser Deposition*. Japanese Journal of Applied Physics, 1993, 32, 4099-4102.	1.5	57
56	Mapping electrostatic potential across an AlGaN/InGaN/AlGaN diode by electron holography. Applied Physics Letters, 2000, 76, 3055-3057.	3.3	57
57	Dynamic observation of defect annealing in CdTe at lattice resolution. Nature, 1982, 298, 127-131.	27.8	55
58	Excimerâ€laserâ€induced crystallization of hydrogenated amorphous silicon. Applied Physics Letters, 1990, 57, 2222-2224.	3.3	54
59	Faultâ€free silicon at the silicon/sapphire interface. Applied Physics Letters, 1982, 41, 371-373.	3.3	53
60	Demonstration of transverse-magnetic deep-ultraviolet stimulated emission from AlGaN multiple-quantum-well lasers grown on a sapphire substrate. Applied Physics Letters, 2015, 106, .	3.3	53
61	Carrier localization and nonradiative recombination in yellow emitting InGaN quantum wells. Applied Physics Letters, 2010, 96, .	3.3	52
62	Investigation of GaN-on-GaN vertical p-n diode with regrown p-GaN by metalorganic chemical vapor deposition. Applied Physics Letters, 2018, 113, .	3.3	52
63	Fine structure of AlNâ•AlGaN superlattice grown by pulsed atomic-layer epitaxy for dislocation filtering. Applied Physics Letters, 2005, 87, 211915.	3.3	49
64	Comprehensive study of the electronic and optical behavior of highly degenerate p-type Mg-doped GaN and AlGaN. Journal of Applied Physics, 2015, 117, .	2.5	49
65	High Voltage Vertical GaN p-n Diodes With Hydrogen-Plasma Based Guard Rings. IEEE Electron Device Letters, 2020, 41, 127-130.	3.9	49
66	Measurement of the piezoelectric field across strained InGaN/GaN layers by electron holography. Solid State Communications, 1999, 111, 281-285.	1.9	48
67	Determination of the atomic structure of inversion domain boundaries in Î±-GaN by transmission electron microscopy. Philosophical Magazine A: Physics of Condensed Matter, Structure, Defects and Mechanical Properties, 1998, 77, 273-286.	0.6	47
68	Study of charge distribution across interfaces in GaN/InGaN/GaN single quantum wells using electron holography. Journal of Applied Physics, 2002, 91, 9856.	2.5	47
69	Growth of highâ€quality AlN layers on sapphire substrates at relatively low temperatures by metalorganic chemical vapor deposition. Physica Status Solidi (B): Basic Research, 2015, 252, 1089-1095.	1.5	46
70	Lattice structure at ZnSeî—¸GaAs heterojunction interfaces prepared by organometallic chemical vapor deposition. Thin Solid Films, 1983, 104, 133-143.	1.8	45
71	Origins of unintentional incorporation of gallium in AlInN layers during epitaxial growth, part I: Growth of AlInN on AlN and effects of prior coating. Journal of Crystal Growth, 2014, 388, 137-142.	1.5	45
72	Polychromatic light emission from single InGaN quantum wells grown on pyramidal GaN facets. Applied Physics Letters, 2005, 87, 131911.	3.3	44

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73	Origins of unintentional incorporation of gallium in InAlN layers during epitaxial growth, part II: Effects of underlying layers and growth chamber conditions. Journal of Crystal Growth, 2014, 388, 143-149.	1.5	44
74	Determination by Electron Holography of the Electronic Charge Distribution at Threading Dislocations in Epitaxial GaN. Physica Status Solidi A, 2002, 192, 407-411.	1.7	42
75	Localized states at InGaN/GaN quantum well interfaces. Applied Physics Letters, 1999, 75, 3835-3837.	3.3	41
76	Bright, Crack-Free InGaN/GaN Light Emitters on Si(111). Physica Status Solidi A, 2002, 192, 308-313.	1.7	41
77	Electron Holography Studies of the Charge on Dislocations in GaN. Physica Status Solidi (B): Basic Research, 2002, 234, 924-930.	1.5	40
78	Misfit dislocations in GaAs heteroepitaxy on (001) Si. Journal of Crystal Growth, 1990, 106, 157-165.	1.5	38
79	Misfit Dislocation Generation in InGaN Epilayers on Free-Standing GaN. Japanese Journal of Applied Physics, 2006, 45, L549-L551.	1.5	38
80	Temperature dependence of the crystalline quality of AlN layer grown on sapphire substrates by metalorganic chemical vapor deposition. Journal of Crystal Growth, 2015, 414, 76-80.	1.5	38
81	Structural and optical characterization of nonpolar GaN/AlN quantum wells. Applied Physics Letters, 2003, 83, 653-655.	3.3	37
82	Localization versus field effects in single InGaN quantum wells. Applied Physics Letters, 2004, 84, 58-60.	3.3	36
83	Sub-250â€‰nm low-threshold deep-ultraviolet AlGaN-based heterostructure laser employing HfO2/SiO2 dielectric mirrors. Applied Physics Letters, 2013, 103, .	3.3	36
84	Low-temperature growth of InGaN films over the entire composition range by MBE. Journal of Crystal Growth, 2015, 425, 115-118.	1.5	36
85	Imaging of the silicon on sapphire interface by highâ€resolution transmission electron microscopy. Applied Physics Letters, 1981, 38, 439-441.	3.3	35
86	Characterisation of dislocations, nanopipes and inversion domains in GaN by transmission electron microscopy. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 1997, 50, 76-81.	3.5	35
87	Highly luminescent, high-indium-content InGaN film with uniform composition and full misfit-strain relaxation. Applied Physics Letters, 2013, 103, .	3.3	35
88	100â€nm thick singleâ€phase wurtzite BAlN films with boron contents over 10%. Physica Status Solidi (B): Basic Research, 2017, 254, 1600699.	1.5	35
89	Summary Abstract: High resolution electron microscopy of CaF2/silicon interfaces. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 1986, 4, 1121.	1.6	34
90	Simple ion milling preparation of ã€ˆ111ã€‰ tungsten tips. Applied Physics Letters, 1989, 54, 1223-1225.	3.3	34

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91	Native tellurium dioxide layer on cadmium telluride: A highâ€resolution electron microscopy study. Applied Physics Letters, 1981, 39, 951-953.	3.3	33
92	Growth of self-assembled GaN quantum dots via the vaporâ€“liquidâ€“solid mechanism. Applied Physics Letters, 2002, 81, 3236-3238.	3.3	33
93	Crystal orientation dependence of the electrical transport and lattice structure of zinc selenide films grown by metalorganic chemical vapor deposition. Journal of Applied Physics, 1985, 58, 1548-1553.	2.5	31
94	Effects of heavy boron doping upon oxygen precipitation in Czochralski silicon. Journal of Applied Physics, 1988, 64, 4454-4465.	2.5	31
95	Characterization of OMVPE-Grown AlGaInN Heterostructures. Materials Research Society Symposia Proceedings, 1996, 449, 509.	0.1	31
96	Effect of layer thickness on the electrostatic potential in InGaN quantum wells. Applied Physics Letters, 2004, 85, 4651-4653.	3.3	31
97	Growth of GaN on ZrB2 substrate by metal-organic vapor phase epitaxy. Applied Surface Science, 2003, 216, 502-507.	6.1	30
98	Atomic arrangement at the Auâ•p-GaN interface in low-resistance contacts. Applied Physics Letters, 2004, 85, 6143-6145.	3.3	30
99	Compositional instability in InAlN/GaN lattice-matched epitaxy. Applied Physics Letters, 2012, 100, .	3.3	30
100	Microstructural properties of Eu-doped GaN luminescent powders. Applied Physics Letters, 2002, 81, 1993-1995.	3.3	29
101	Sub 250â€‰nm deep-UV AlGaN/AlN distributed Bragg reflectors. Applied Physics Letters, 2017, 110, .	3.3	29
102	The effect of a Ga prelayer on the beginning of GaAs epitaxy on Si. Journal of Applied Physics, 1988, 64, 3472-3475.	2.5	28
103	Polarity determination and atomic arrangements at a GaN/SiC interface using high-resolution image matching. Applied Physics Letters, 2000, 76, 822-824.	3.3	28
104	Simulations, Practical Limitations, and Novel Growth Technology for InGaN-Based Solar Cells. IEEE Journal of Photovoltaics, 2014, 4, 601-606.	2.5	28
105	Plasticity and optical properties of GaN under highly localized nanoindentation stress fields. Journal of Applied Physics, 2017, 121, .	2.5	28
106	Implantation-and etching-free high voltage vertical GaN pâ€“n diodes terminated by plasma-hydrogenated p-GaN: revealing the role of thermal annealing. Applied Physics Express, 2019, 12, 051015.	2.4	28
107	Gradedâ€thickness samples for molecular beam epitaxial growth studies of GaAs/Si heteroepitaxy. Applied Physics Letters, 1988, 52, 1779-1781.	3.3	27
108	Atomic arrangement at the AlN/ZrB2 interface. Applied Physics Letters, 2002, 81, 3182-3184.	3.3	27

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109	Dislocation generation at the coalescence of aluminum nitride lateral epitaxy on shallow-grooved sapphire substrates. Applied Physics Letters, 2007, 90, 221909.	3.3	27
110	High-resolution transmission electron microscopy of 60[ddot] dislocations in si-GaAs. Philosophical Magazine A: Physics of Condensed Matter, Structure, Defects and Mechanical Properties, 1989, 59, 1045-1058.	0.6	26
111	Mapping the electrostatic potential across AlGaNâˆ•AlNâˆ•GaN heterostructures using electron holography. Applied Physics Letters, 2007, 90, 032101.	3.3	26
112	Blue light emitting diodes grown on freestanding (11-20) a-plane GaN substrates. Applied Physics Letters, 2008, 92, 011123.	3.3	26
113	Refractory In$_{x}$ Ga1âˆ’$_{x}$ N Solar Cells for High-Temperature Applications. IEEE Journal of Photovoltaics, 2017, 7, 1646-1652.	2.5	26
114	CdCl2 passivation of polycrystalline CdMgTe and CdZnTe absorbers for tandem photovoltaic cells. Journal of Applied Physics, 2018, 123, .	2.5	26
115	Defect formation near GaN surfaces and interfaces. Physica B: Condensed Matter, 1999, 273-274, 70-74.	2.7	25
116	Optoelectronic and microstructure attributes of epitaxial SrTiO3 on Si. Journal of Applied Physics, 2005, 97, 014101.	2.5	25
117	Effect of internal electrostatic fields in InGaN quantum wells on the properties of green light emitting diodes. Applied Physics Letters, 2007, 91, .	3.3	25
118	Non-uniform Mg distribution in GaN epilayers grown on mesa structures for applications in GaN power electronics. Applied Physics Letters, 2019, 114, .	3.3	25
119	GaN Vertical-Channel Junction Field-Effect Transistors With Regrown p-GaN by MOCVD. IEEE Transactions on Electron Devices, 2020, 67, 3972-3977.	3.0	25
120	Use of ZnSe as an interlayer for GaAs growth on Si. Applied Physics Letters, 1992, 61, 195-197.	3.3	24
121	Observation of coreless edge and mixed dislocations in Mg-doped Al0.03Ga0.97N. Applied Physics Letters, 2002, 81, 4541-4543.	3.3	24
122	Role of the buffer layer thickness on the formation of basal plane stacking faults in a-plane GaN epitaxy on r-sapphire. Applied Physics Letters, 2008, 93, 011901.	3.3	24
123	Optimization of growth conditions for InGaAs/InAlAs/InP quantum cascade lasers by metalorganic chemical vapor deposition. Journal of Crystal Growth, 2011, 316, 75-80.	1.5	24
124	Onset of surface stimulated emission at 260â€‰nm from AlGaN multiple quantum wells. Applied Physics Letters, 2015, 107, .	3.3	24
125	Interface effects in amorphous silicon/nitride multilayers. Journal of Non-Crystalline Solids, 1985, 77-78, 995-998.	3.1	23
126	Depth-resolved electron-excited nanoscale-luminescence spectroscopy studies of defects near GaN/InGaN/GaN quantum wells. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 1999, 17, 2545.	1.6	23

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127	A Comparison of Rutherford Backscattering Spectroscopy and X-Ray Diffraction to Determine the Composition of Thick InGaN Epilayers. Physica Status Solidi (B): Basic Research, 2001, 228, 41-44.	1.5	23
128	Metalâ€“Organic Hydride Vapor Phase Epitaxy of AlxGa1-xN Films over Sapphire. Japanese Journal of Applied Physics, 2007, 46, L752-L754.	1.5	23
129	High-resolution lattice imaging of cadmium telluride. Philosophical Magazine A: Physics of Condensed Matter, Structure, Defects and Mechanical Properties, 1982, 45, 693-711.	0.6	22
130	Nanopipes and Inversion Domains in High-Quality GaN Epitaxial Layers. Materials Research Society Symposia Proceedings, 1996, 449, 405.	0.1	22
131	Microstructure of InGaN Quantum Wells. Materials Research Society Symposia Proceedings, 1997, 482, 31.	0.1	22
132	High-Quality GaN heteroepitaxial films grown by metalorganic chemical vapor deposition. Journal of Electronic Materials, 1995, 24, 257-261.	2.2	21
133	Microscopic correlation of redshifted luminescence and surface defects in thick InxGa1â^'xN layers. Applied Physics Letters, 2002, 80, 3524-3526.	3.3	21
134	Defect and stress control of AlGaN for fabrication of high performance UV light emitters. Physica Status Solidi A, 2004, 201, 2679-2685.	1.7	21
135	Optical properties of highly luminescent zinc oxide tetrapod powders. Applied Physics Letters, 2007, 91, 121905.	3.3	21
136	Atomic Arrangement at the AlN/Si(110) Interface. Applied Physics Express, 0, 1, 061104.	2.4	21
137	Comparative Study on MOCVD Growth of a-Plane GaN Films on r-Plane Sapphire Substrates Using GaN, AlGaN, and AlN Buffer Layers. Journal of Electronic Materials, 2009, 38, 1938-1943.	2.2	21
138	Optically pumped vertical-cavity surface-emitting laser at 374.9 nm with an electrically conducting n-type distributed Bragg reflector. Applied Physics Express, 2016, 9, 111002.	2.4	21
139	Selective area regrowth and doping for vertical gallium nitride power devices: Materials challenges and recent progress. Materials Today, 2021, 49, 296-323.	14.2	21
140	Critical thickness determination of InAs, InP and GaP on GaAs by X-ray interference effect and transmission electron microscopy. Journal of Crystal Growth, 1993, 131, 465-469.	1.5	20
141	Epitaxial growth of AlxGa1â^'xN on Si(111) via a ZrB2(0001) buffer layer. Applied Physics Letters, 2004, 84, 3510-3512.	3.3	20
142	Strain Relaxation Mechanisms in AlGaN Epitaxy on AlN Templates. Applied Physics Express, 2010, 3, 111003.	2.4	20
143	Time-resolved cathodoluminescence of Mg-doped GaN. Applied Physics Letters, 2008, 93, .	3.3	19
144	Inâ€plane polarization of GaNâ€based heterostructures with arbitrary crystal orientation. Physica Status Solidi (A) Applications and Materials Science, 2010, 207, 2226-2232.	1.8	19

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145	The effect of InGaN underlayers on the electronic and optical properties of InGaN/GaN quantum wells. Applied Physics Letters, 2013, 102, .	3.3	19
146	A review of the synthesis of reduced defect density InxGa1â^'xN for all indium compositions. Solid-State Electronics, 2017, 136, 3-11.	1.4	19
147	Dopant profiling in p-i-n GaN structures using secondary electrons. Journal of Applied Physics, 2019, 126, .	2.5	19
148	Microscopic aspects of oxygen precipitation in silicon. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 1989, 4, 11-17.	3.5	18
149	Gallium-nitride-based devices on silicon. Physica Status Solidi C: Current Topics in Solid State Physics, 2003, 0, 1940-1949.	0.8	18
150	Mechanism of H2 pre-annealing on the growth of GaN on sapphire by MOVPE. Applied Surface Science, 2003, 216, 585-589.	6.1	17
151	Correlation of spectral luminescence with threading dislocations in green-light-emitting InGaN quantum wells. Applied Physics Letters, 2007, 90, 231901.	3.3	17
152	Highly conductive modulation doped composition graded p-AlGaN/(AlN)/GaN multiheterostructures grown by metalorganic vapor phase epitaxy. Journal of Applied Physics, 2009, 106, .	2.5	17
153	Ammonothermal growth of high-quality GaN crystals on HVPE template seeds. Journal of Crystal Growth, 2011, 318, 1030-1033.	1.5	17
154	InAs quantum dot growth on AlxGa1â^'xAs by metalorganic vapor phase epitaxy for intermediate band solar cells. Journal of Applied Physics, 2014, 116, .	2.5	17
155	Origin of high hole concentrations in Mgâ€doped GaN films. Physica Status Solidi (B): Basic Research, 2017, 254, 1600668.	1.5	17
156	Crystal structure and composition of BAlN thin films: Effect of boron concentration in the gas flow. Journal of Crystal Growth, 2017, 475, 334-340.	1.5	17
157	Interface properties of n-ZnSeâ€"p-Ge heterojunctions grown by organometallic chemical vapor deposition. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 1983, 1, 656.	1.6	16
158	HgTeâ€"CdTe superlattices grown on lattice-mismatched GaAs substrates. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 1986, 4, 1306.	1.6	16
159	C^{â^'} Outgrowths in C⁺ Thin Films of LiNbO₃ on Al₂O₃-c. Materials Research Society Symposia Proceedings, 1994, 341, 289.	0.1	16
160	Spatial variation of luminescence in thick GaN films. Applied Physics Letters, 2001, 78, 1222-1224.	3.3	16
161	Spatial variation of luminescence from AlGaN grown by facet controlled epitaxial lateral overgrowth. Applied Physics Letters, 2004, 85, 3417-3419.	3.3	16
162	Lateral Current Spreading in III-N Ultraviolet Vertical-Cavity Surface-Emitting Lasers Using Modulation-Doped Short Period Superlattices. IEEE Journal of Quantum Electronics, 2018, 54, 1-7.	1.9	16

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163	Structure of Thermally-Induced Microdefects in Czochralski Silicon. Materials Research Society Symposia Proceedings, 1983, 31, 153.	0.1	15
164	Initial Stages of GaAs Epitaxy on Si. Materials Research Society Symposia Proceedings, 1988, 116, 33.	0.1	15
165	Structure and luminescence of nanocrystalline gallium nitride synthesized by a novel polymer pyrolysis route. Optical Materials, 2006, 29, 19-23.	3.6	15
166	Effect of misfit dislocations on luminescence in m-plane InGaN quantum wells. Applied Physics Letters, 2011, 98, 261914.	3.3	15
167	Improved optical properties of InAs quantum dots for intermediate band solar cells by suppression of misfit strain relaxation. Journal of Applied Physics, 2016, 120, .	2.5	15
168	Current transport mechanisms in GaAs/AlAs tunnel structures grown by metalâ€“organic chemical vapor deposition. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 1986, 4, 988.	1.6	14
169	The transition from As-doped GaN, showing blue emission, to GaNAs alloys in films grown by molecular beam epitaxy. Journal of Crystal Growth, 2002, 240, 423-430.	1.5	14
170	The generation of misfit dislocations in facet-controlled growth of AlGaNâ•GaN films. Applied Physics Letters, 2004, 85, 4923-4925.	3.3	14
171	Growth of InN on Ge substrate by molecular beam epitaxy. Journal of Crystal Growth, 2005, 279, 311-315.	1.5	14
172	Transmission electron microscopy study of GaInNAs(Sb) thin films grown by atomic hydrogen-assisted molecular beam epitaxy. Applied Physics Letters, 2011, 99, 191907.	3.3	14
173	Strain-related optical properties of ZnO crystals due to nanoindentation on various surface orientations. Journal of Applied Physics, 2013, 113, 183511.	2.5	14
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